

**QIAOXIN N-Channel Super Trench II Power MOSFET**

**Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

**Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

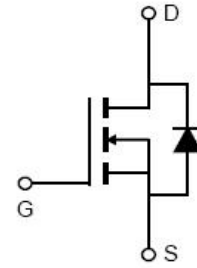
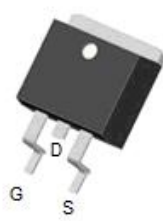
**General Features**

- $V_{DS} = 100V, I_D = 135A$   
 $R_{DS(ON)} = 3.65m\Omega$ , typical (TO-220)@  $V_{GS} = 10V$   
 $R_{DS(ON)} = 3.5m\Omega$ , typical (TO-263)@  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- Pb-free Mold Compound

**TO-220**



**TO-263**



**Schematic Diagram**

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VCR039N10	VCR039N10	TO-220	-	-	-
VCR039N10D	VCR039N10D	TO-263	-	-	-

**Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous	$I_D$	135	A
Drain Current-Continuous(T <sub>c</sub> =100°C)	$I_D(100^\circ C)$	108	A
Pulsed Drain Current	$I_{DM}$	540	A
Maximum Power Dissipation	$P_D$	220	W
Derating factor		1.47	W/°C
Single pulse avalanche energy (Note 1)	$E_{AS}$	730	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.68	°C/W
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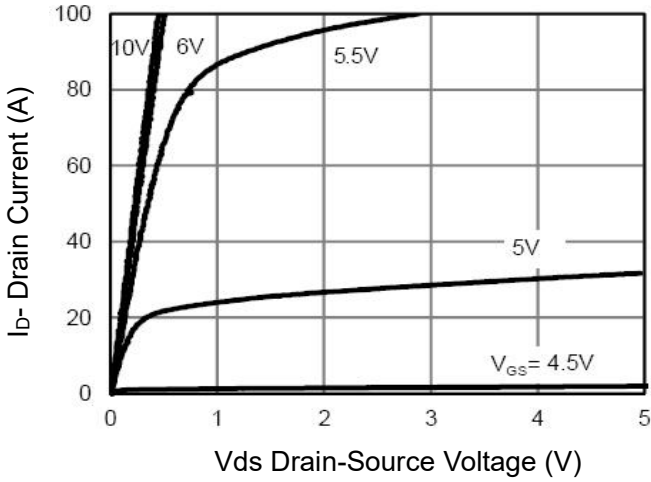
### Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100		-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA	
<b>On Characteristics</b>							
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =65A	TO-220	-	3.65	3.9	mΩ
			TO-263		3.5	3.9	mΩ
Gate resistance	R <sub>G</sub>		-	1.5	-	Ω	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =65A		90	-	S	
<b>Dynamic Characteristics</b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1.0MHz	-	9500	-	PF	
Output Capacitance	C <sub>oss</sub>		-	650	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	40	-	PF	
<b>Switching Characteristics</b> (Note 2)							
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, I <sub>D</sub> =65A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	20	-	nS	
Turn-on Rise Time	t <sub>r</sub>		-	11.5	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	48	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =65A, V <sub>GS</sub> =10V	-	125	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	40.5	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>		-	33	-	nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =65A	-		1.2	V	
Diode Forward Current	I <sub>S</sub>		-	-	135	A	
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub> di/dt = 100A/μs	-	76	-	nS	
Reverse Recovery Charge	Q <sub>rr</sub>		-	150	-	nC	

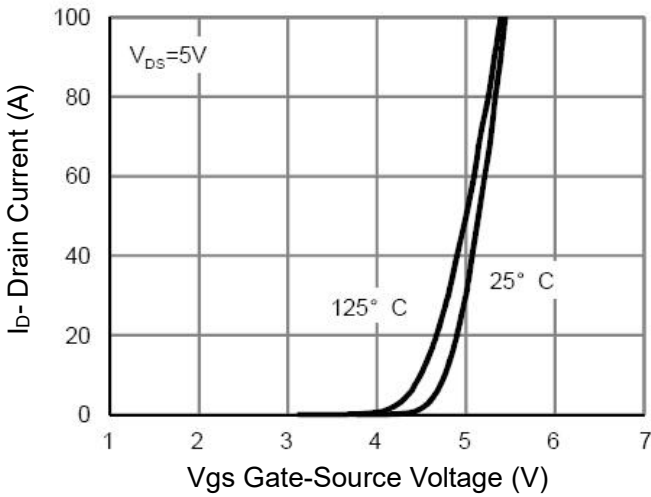
#### Notes:

1. EAS condition : T<sub>j</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J</sub>(MAX)=175° C. The SOA curve provides a single pulse rating.

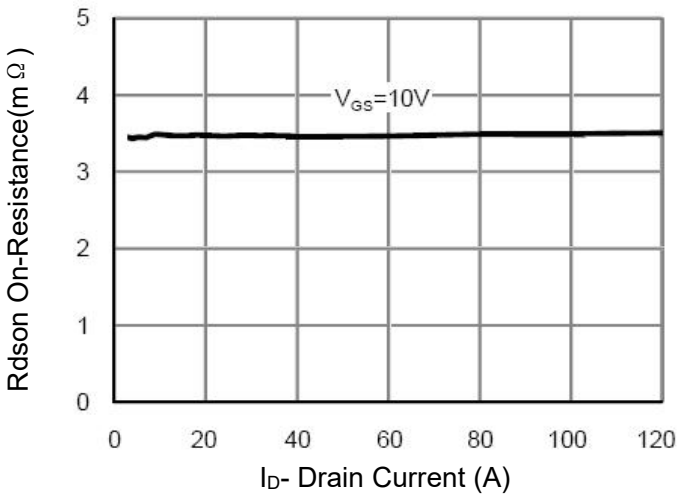
**Typical Electrical and Thermal Characteristics**



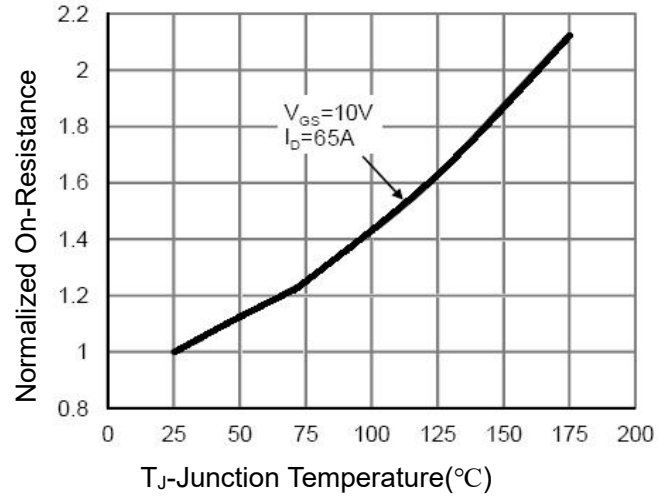
**Figure 1 Output Characteristics**



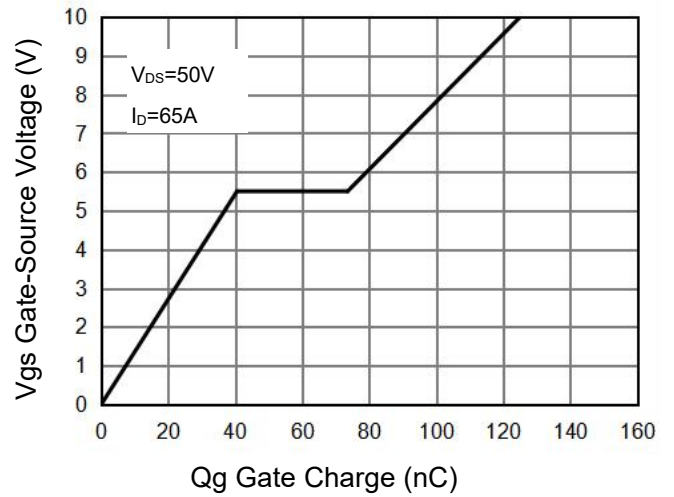
**Figure 2 Transfer Characteristics**



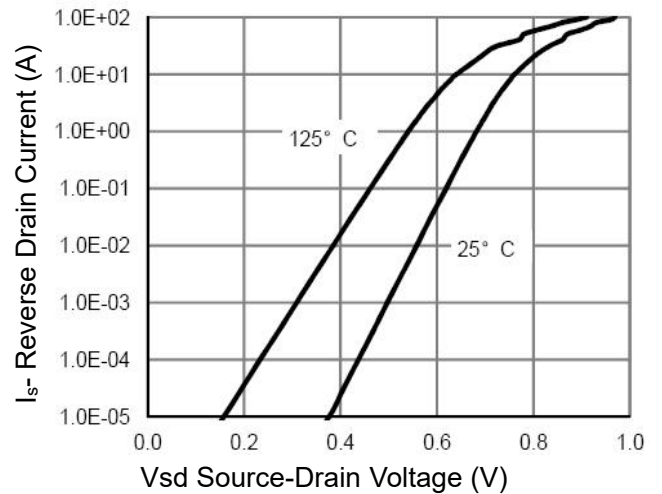
**Figure 3 Rdson- Drain Current**



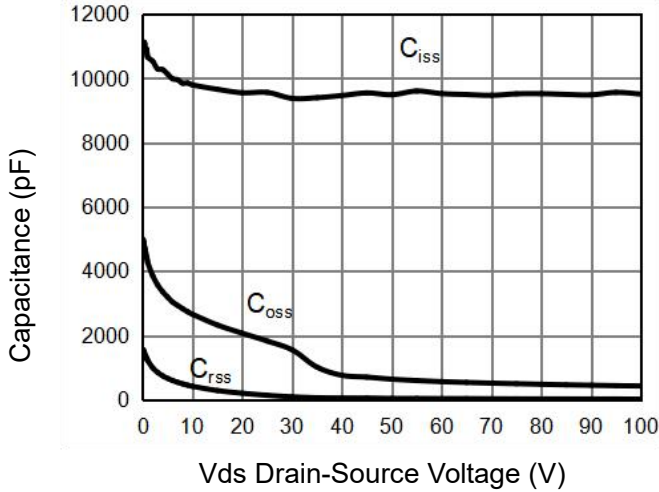
**Figure 4 Rdson-Junction Temperature**



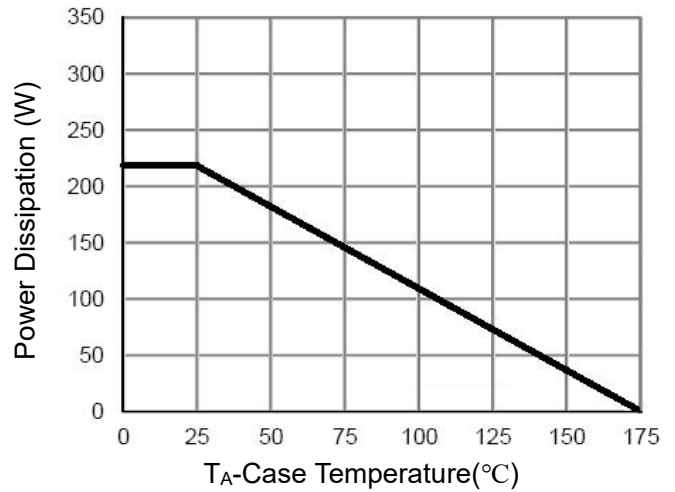
**Figure 5 Gate Charge**



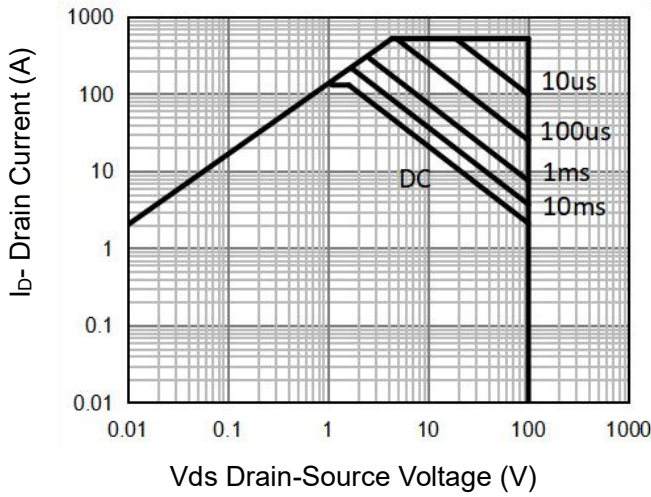
**Figure 6 Source- Drain Diode Forward**



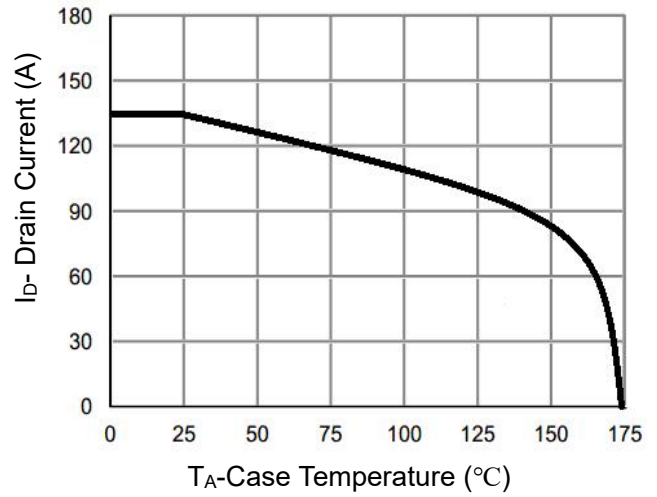
**Figure 7 Capacitance vs Vds**



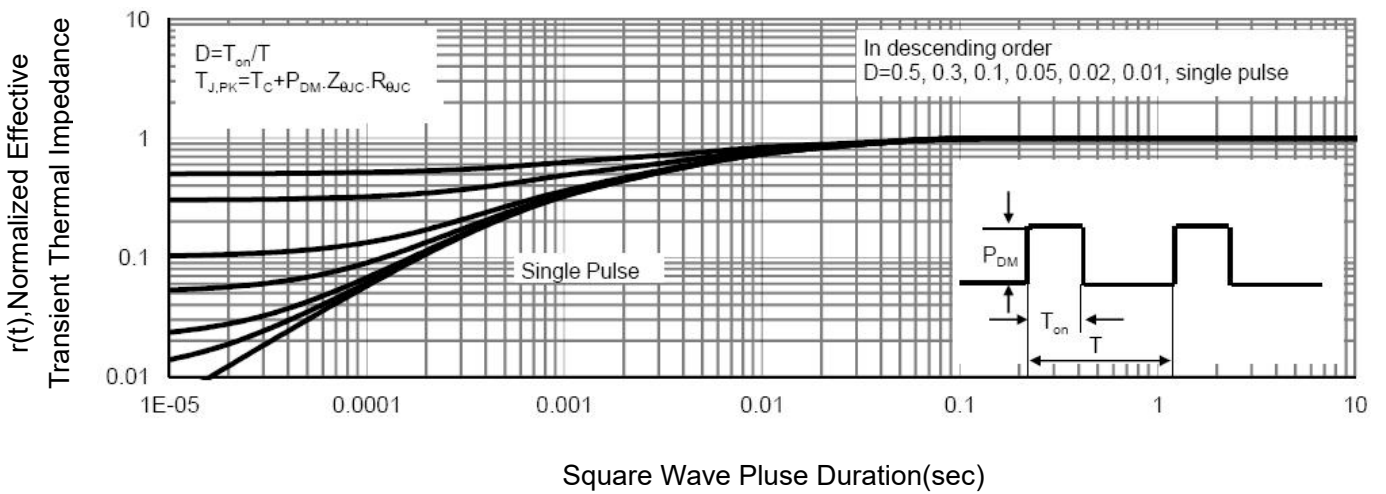
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

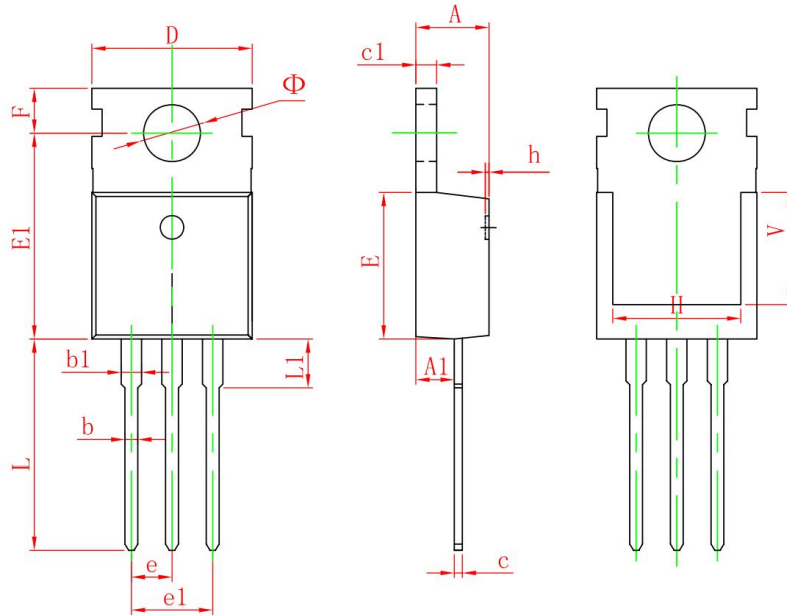


**Figure 10 Current De-rating**



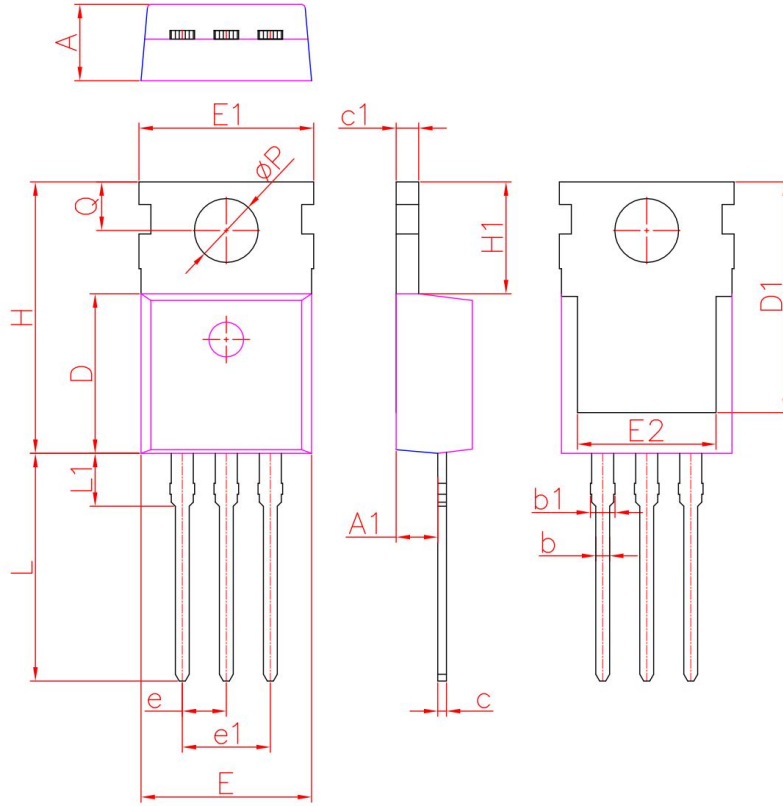
**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-220-3L(C) Package Information**



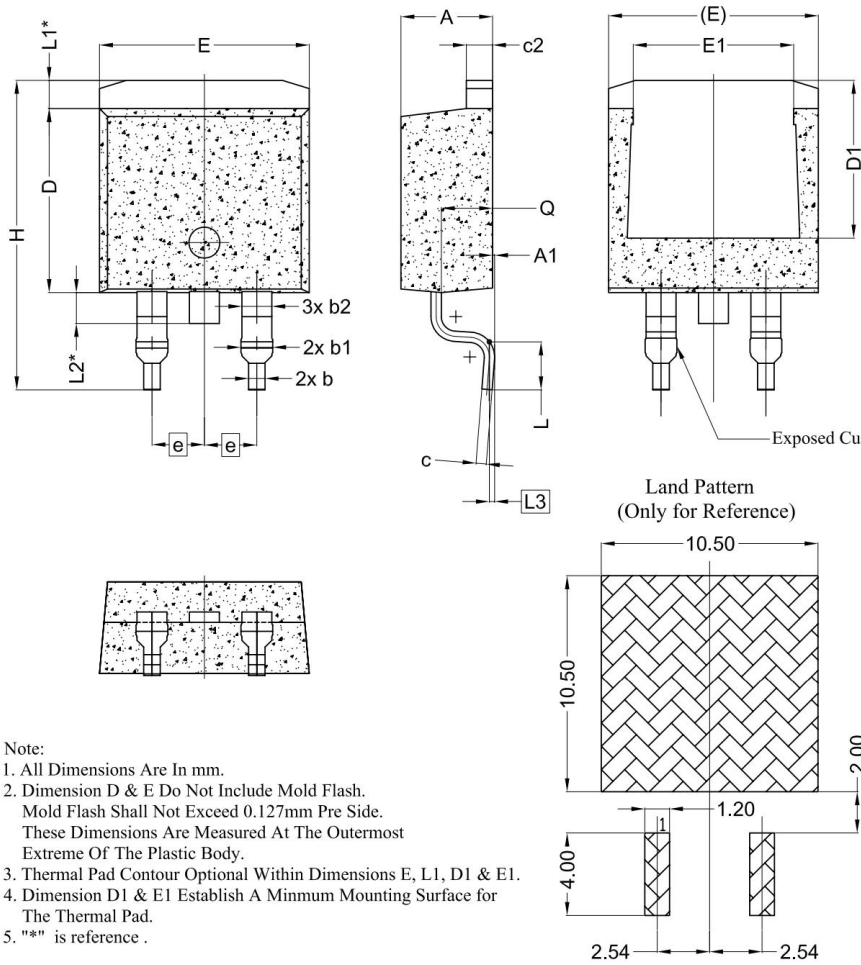
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

**TO-220-3L(E) Package Information**



TO220			
DIM.	MIN.	NOM.	MAX.
A	4.20	4.40	4.60
A1	2.25	2.40	2.55
b	0.70	0.80	0.90
b1	1.17	1.27	1.37
c	0.33	0.50	0.65
c1	1.20	1.30	1.40
D	8.95	9.20	9.75
D1	13.10	13.30	13.50
E	9.74	9.84	10.04
E1	9.91	10.08	10.25
E2	7.90	8.00	8.10
e	2.54BSC		
e1	5.08BSC		
H	15.45	15.65	15.85
H1	6.30	6.45	6.60
L	12.90	13.13	13.40
L1	2.85	3.05	3.25
Q	2.65	2.80	2.95
øP	3.40	3.68	3.80
All dimensions in millimeters			

**TO-263-2L(G) Package Information**

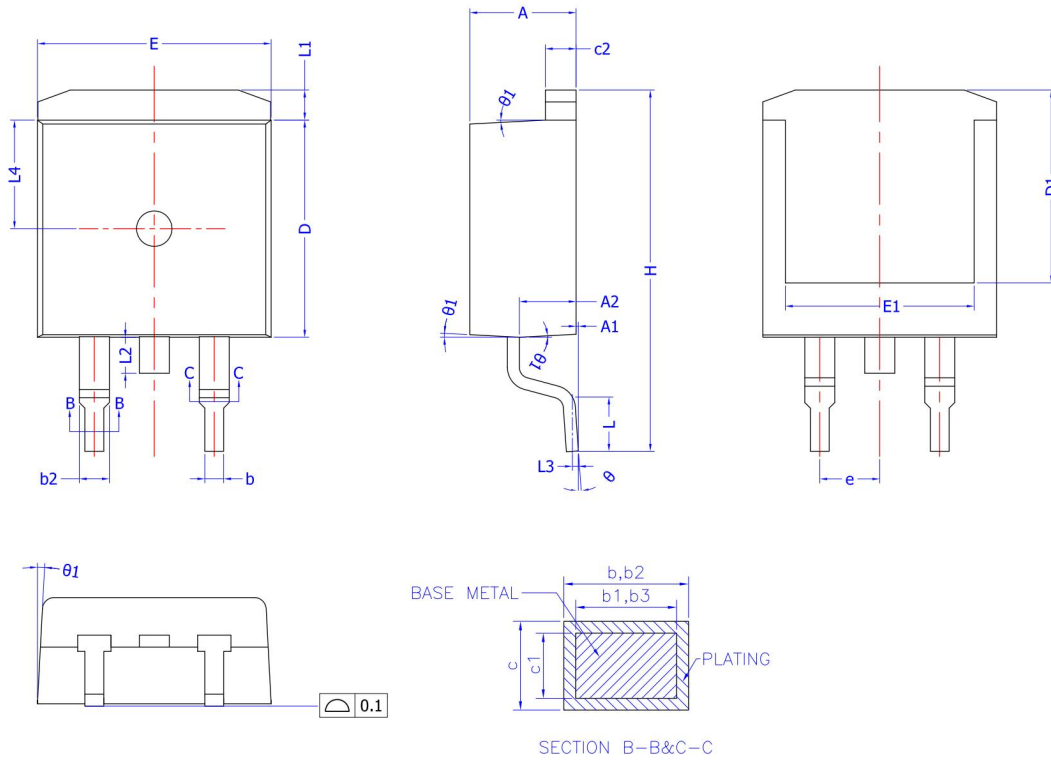


- Note:
1. All Dimensions Are In mm.
  2. Dimension D & E Do Not Include Mold Flash.  
Mold Flash Shall Not Exceed 0.127mm Pre Side.  
These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
  3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
  4. Dimension D1 & E1 Establish A Minmum Mounting Surface for The Thermal Pad.
  5. "\*" is reference .

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



**TO-263-2L(P) Package Information**

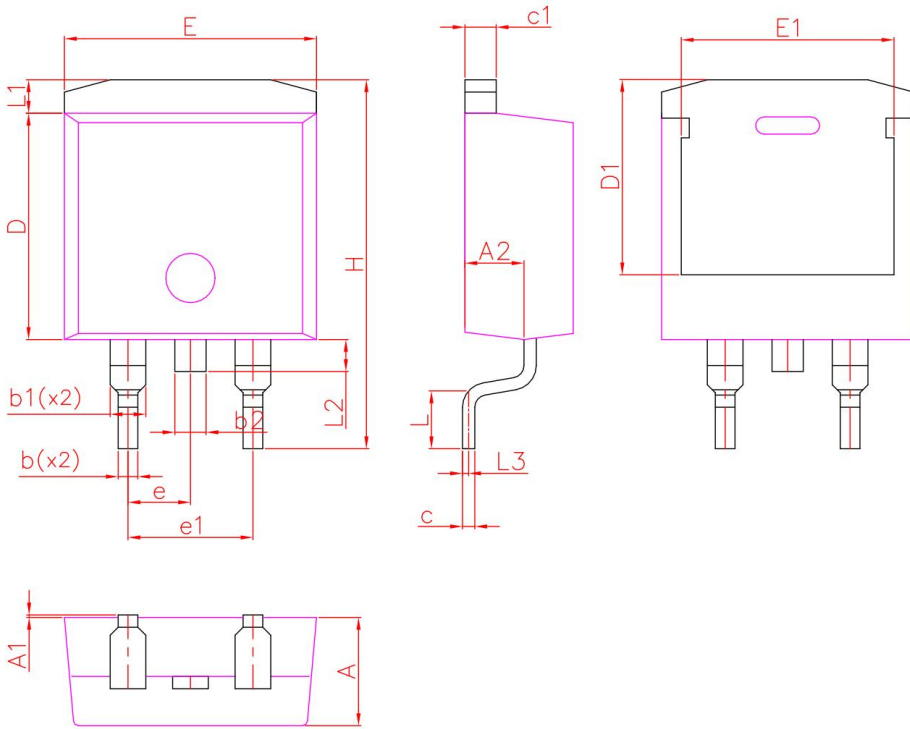


**COMMON DIMENSIONS  
(UNITS OF MEASURE =MILLIMETER)**

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	---	8°
θ1	1°	3°	5°



**TO-263-2L(E) Package Information**



T0263			
DIM.	MIN.	NOM.	MAX.
A	4.20	4.40	4.60
A1	0.00	0.10	0.25
A2	2.20	2.40	2.60
b	0.70	0.80	0.90
b1	1.20	1.45	1.75
b2	1.17	1.27	1.37
c	0.40	0.50	0.60
c1	1.15	1.27	1.40
D	9.10	9.20	9.30
D1	7.63	7.93	8.23
E	10.05	10.25	10.45
E1	8.35	8.65	8.95
e	2.54BSC		
e1	5.08BSC		
H	14.61	15.00	15.88
L	1.78	2.35	2.79
L1	1.36REF		
L2	1.3REF		
L3	0.25REF		
All dimensions in millimeters			

### Attention

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